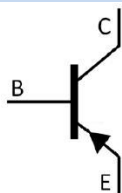


SOT-23 PNP Silicon PNP transistor in a SOT-23 Plastic Package.

, , KSC3265
 High h_{FE} , low saturation voltage, complementary pair with KSC3265.

Low frequency power amplifier, power switching application.

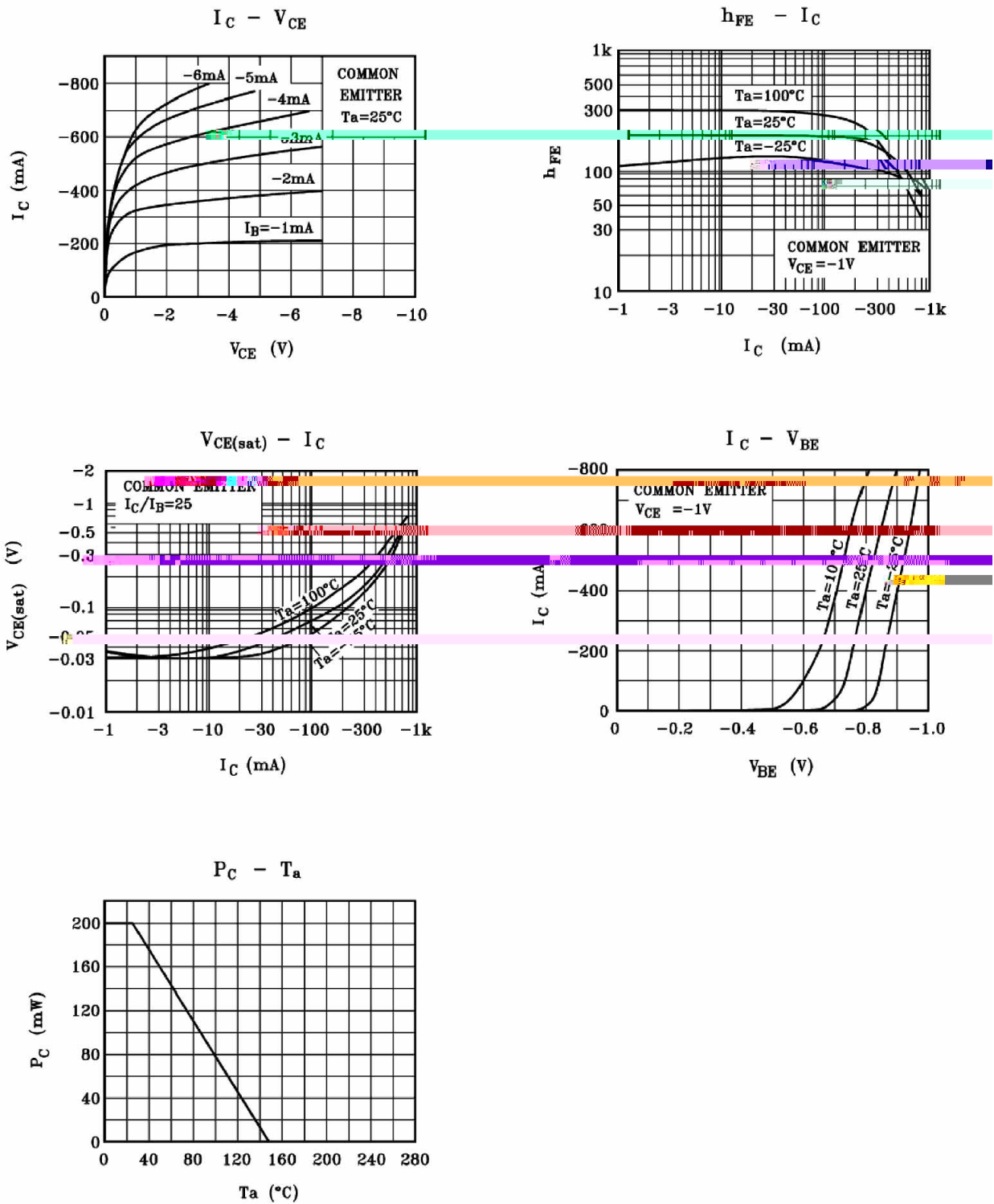


PIN 1 Base PIN 2 Emitter PIN 3 Collector

h_{FE} Classifications Symbol	O	Y
h_{FE} Range	100 200	160 320
Marking	HIO	HIY

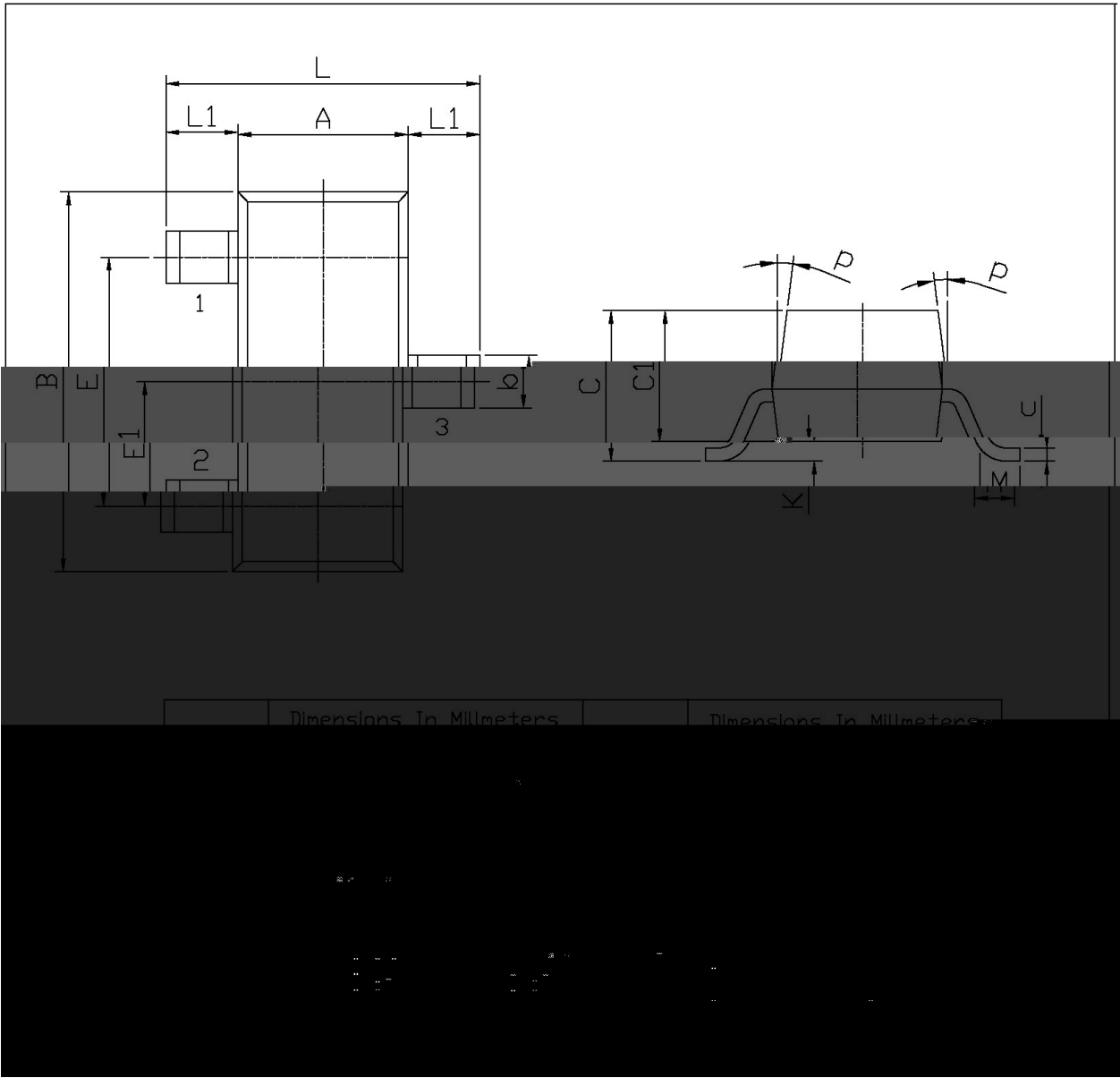
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-35	V
Collector to Emitter Voltage	V_{CEO}	-30	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current	I_C	-800	mA
Base Current	I_B	-160	mA
Collector Power Dissipation	P_C	200	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

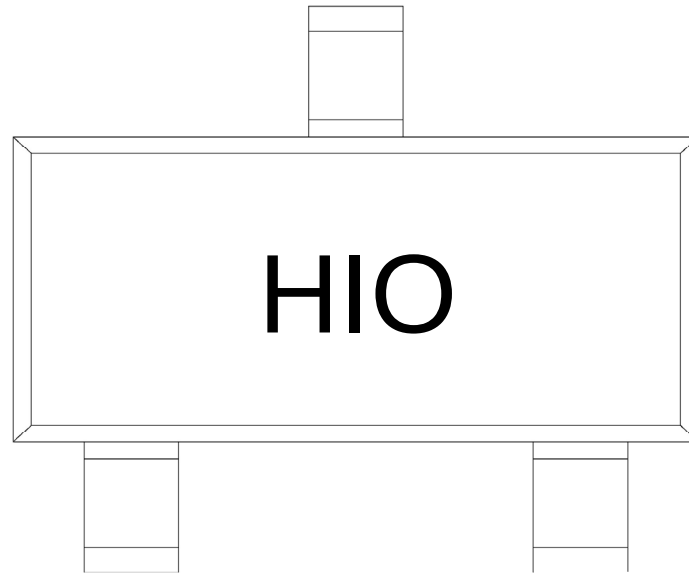
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Emitter Breakdown Voltage	V_{CEO}	$I_C = -10mA$ $I_B = 0$	-30			V
Collector to Emitter Breakdown Voltage	V_{EBO}	$I_E = -1.0mA$ $I_C = 0$	-5.0			V
Collector Cut-Off Current	I_{CBO}	$V_{CB} = -30V$ $I_E = 0$			-0.1	μA
Emitter Cut-Off Current	I_{EBO}	$V_{EB} = -5.0V$ $I_C = 0$			-0.1	μA
DC Current Gain	$h_{FE(1)}$	$V_{CE} = -1.0V$ $I_C = -100mA$	100		320	
	$h_{FE(2)}$	$V_{CE} = -1.0V$ $I_C = -800mA$	40			
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = -500mA$ $I_B = -20mA$			-0.4	V
Base to Emitter Voltage	V_{BE}	$V_{CE} = -1.0V$ $I_C = -10mA$	-0.5		-0.8	V
Transition Frequency	f_T	$V_{CE} = -5.0V$ $I_C = -10mA$		120		MHz
Collector Output Capacitance	C_{ob}	$V_{CB} = -10V$ $f = 1.0MHz$ $I_E = 0$		13		pF



SOT-23

单位；mm





H

I

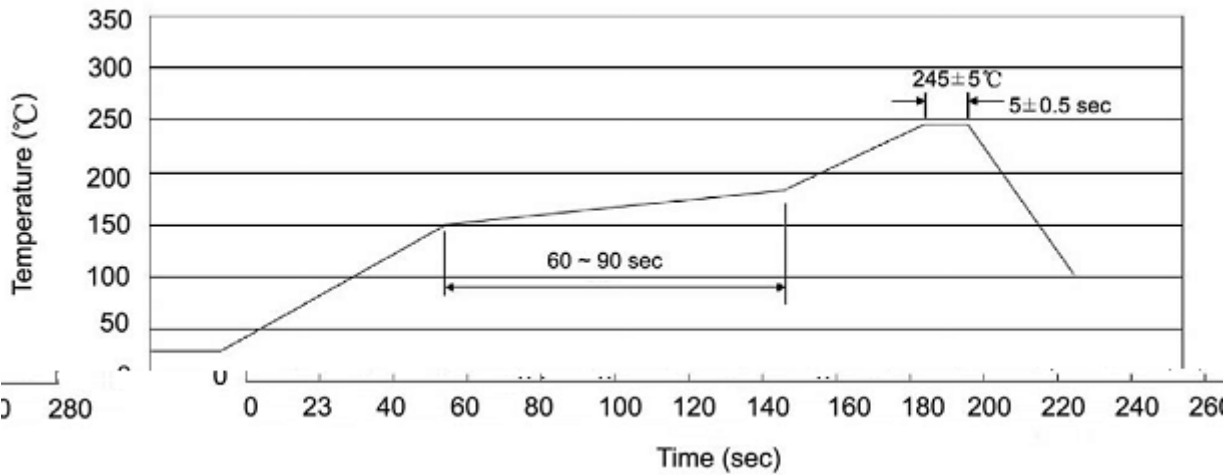
O h_{FE}

Note:

H Company Code

I Product Type

O h_{FE} Classifications Symbol



Note:

- 1

25 150

60 90sec;

1.Preheating:25~150 , Time:60~90sec.
- 2

245±5

5±0.5sec;

2.Peak Temp.:245±5 , Duration:5±0.5sec.
- 3

2 10 /sec.

3. Cooling Speed: 2~10 /sec.

260±5

10±1 sec.

Temp.:260±5

Time:10±1 sec

/ REEL

Package Type	Units					Dimension (unit mm ³)		